#	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 6188101 B1	20010213	5	Flash EPROM cell with reduced short channel effect and method for providing	257/314	257/315; 257/404; 257/640; 257/914	Wang, Janet
2	US 6054731 A	20000425	9	Floating gate non-volatile memory cell with low erasing voltage and manufacturing method same	257/314	257/316; 257/324	Cappelletti, Paolo
3	US 6172394 B1	20010109	16	Non-volatile semiconductor memory device having a floating gate with protruding conductive side-wall portions	257/315	257/288; 257/387; 438/257; 438/304	Nakagawa, Shinichi
4	US 6130452 A	20001010	16	Virtual ground flash cell with asymmetrically placed source and drain and method of fabrication	257/315	257/321	Lu, Wenpin, et al.
5	US 5753952 A	19980519	11	Nonvolatile memory cell with P-N junction formed in polysilicon floating gate	257/316	257/315; 257/317; 257/318; 365/185.01; 365/185.1; 438/264	Mehrad, Freidoon
6	US 5619051 A	19970408	11	Semiconductor nonvolatile memory cell	257/316	257/324; 257/325; 257/411	Endo, Nobuhiro
7	US 6144062 A	20001107	35	Semiconductor device having thin electrode layer adjacent gate insulator and method of manufacture	257/317	257/315; 257/321	Mine, Toshiyuki, et al.
8	US 5780093 A	19980714	13	Non-volatile semiconductor memory device including memory transistor with a composite gate structure	257/318	257/262; 257/264; 257/314; 257/315; 257/316; 257/317; 257/322	Sugaya, Fumitaka
9	US 5319229 A	19940607	18	Semiconductor nonvolatile memory with wide memory window and long data retention time	257/324	257/406; 257/411; 257/637; 257/640; 257/645; 438/287	Shimoji, Noriyuki, et al.

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10 US 6236085 B1	20010522	25	Semiconductor memory device having high-concentration region around electric-field moderating layer in substrate	257/345	257/315 ; 257/316 ; 257/318 ; 257/319 ; 257/320 ; 257/321 ; 257/322 ; 257/336 ; 257/344 ; 257/408 ; 257/900	Kawaguchi, Tsutomu , et al.
11 US 6137718 A	20001024	6	Method for operating a non-volatile memory cell arrangement	365/185.03	257/324 ; 365/185.28	Reisinger, Hans
12 US 4996571 A	19910226	15	Non-volatile semiconductor memory device erasing operation	365/185.19	257/321 ; 365/185.06 ; 365/185.09 ; 365/185.23 ; 365/185.3 ; 365/218	Kume, Hitoshi , et al.
13 US 5432749 A	19950711	7	Non-volatile memory cell having hole confinement layer for reducing band-to-band tunneling	365/185.03	257/315 ; 365/185.17	Sethi, Rakesh B.
14 US 5904518 A	19990518	18	Method of manufacturing a semiconductor IC device having single transistor type nonvolatile memory cells	438/201	438/258	Komori, Kazuhiro , et al.
15 US 6238967 B1	20010529	14	Method of forming embedded DRAM structure	438/244	438/243	Shiho, Yasuhito , et al.
16 US 5814543 A	19980929	35	Method of manufacturing a semiconductor integrated circuit device having nonvolatile memory cells	438/264	438/265 ; 438/592	Nishimoto, Toshiaki , et al.

	Type	Hits	Search Text	DBs	Time Stamp
1	IS&R	10	(("4577215") or ("5482879") or ("5879992") or ("6229176") or ("5016068") or ("5295107") or ("6046086") or ("4442447") or ("4513397") or ("4592130")).PN.	USPAT: US-PGPUB	2001/09/17 08:33
2	IS&R	40	(("4618876") or ("4903097") or ("5526307") or ("5760435") or ("6069381") or ("6207989") or ("6239465") or ("4417264") or ("4558339") or ("4590665") or ("4802137") or ("5212541") or ("5216268") or ("5216269") or ("5289026") or ("5292681") or ("5432109") or ("5447877") or ("5457061") or ("5595920") or ("5605853") or ("5612237") or ("5625213") or ("5702965") or ("5801993") or ("5814543") or ("5851880") or ("5852312") or ("5858840") or ("5877525") or ("5940705") or ("5946240") or ("5950087") or ("5972753") or ("6034892") or ("6037226") or ("6093607") or ("6124168") or ("6180977") or ("6188102")).PN.	USPAT: US-PGPUB	2001/09/17 08:33
3	IS&R	54	("438/288").CCLS.	USPAT: US-PGPUB	2001/09/17 09:30
4	IS&R	652	("257/315").CCLS.	USPAT: US-PGPUB	2001/09/17 09:56
5	IS&R	309	("257/324").CCLS.	USPAT: US-PGPUB	2001/09/17 09:56
6	BRS	267	(("257/324").CCLS.) not (("257/315").CCLS.)	USPAT: US-PGPUB	2001/09/17 09:57
7	BRS	342	asymmetric same source same drain	USPAT: US-PGPUB	2001/09/17 11:13
8	BRS	240	asymmetric with source with drain	USPAT: US-PGPUB	2001/09/17 11:13
9	BRS	159	(asymmetric with source with drain) and memory	USPAT: US-PGPUB	2001/09/17 11:14